

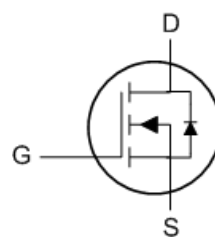
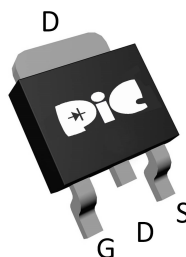
➤ General Description

This PAN18TX20AX N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ TO-252



➤ Application

- Switch application
- DC/DC Converters Power
- Tools

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D@T_C=25^\circ C$	16	A
Continuous Drain Current ¹	$I_D@T_C=100^\circ C$	10	A
Continuous Drain Current ¹	$I_D@T_A=25^\circ C$	2.7	A
Continuous Drain Current ¹	$I_D@T_A=70^\circ C$	2.2	A
Pulsed Drain Current ²	I_{DM}	32	A
Single Pulse Avalanche Energy ³	EAS	39.2	mJ
Avalanche Current	I_{AS}	28	A
Total Power Dissipation ⁴	$P_D@T_C=25^\circ C$	69	W
Total Power Dissipation ⁴	$P_D@T_A=25^\circ C$	2	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	62	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	1.8	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	BV_{DSS}	200	---	---	V
Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=10A$	$R_{DS(ON)}$	---	96	120	$m\Omega$
Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	$V_{GS(th)}$	2.0	---	3.5	V
Drain-Source Leakage Current	$V_{DS}=160V$, $V_{GS}=0V$, $T_J=25^\circ C$	I_{DSS}	---	---	1	μA
	$V_{DS}=160V$, $V_{GS}=0V$, $T_J=55^\circ C$		---	---	5	
Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	I_{GSS}	---	---	± 100	nA
Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	R_g	---	0.9	---	Ω
Total Gate Charge (10V)	$V_{DS}=100V$, $V_{GS}=10V$, $I_D=10A$	Q_g	---	13.7	---	nC
Gate-Source Charge		Q_{gs}	---	3.7	---	
Gate-Drain Charge		Q_{gd}	---	3.3	---	
Turn-On Delay Time	$V_{DD}=100V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=10A$	$T_{d(on)}$	---	8.3	---	ns
Rise Time		T_r	---	19	---	
Turn-Off Delay Time		$T_{d(off)}$	---	14.7	---	
Fall Time		T_f	---	3.9	---	
Input Capacitance	$V_{DS}=100V$, $V_{GS}=0V$, $f=1MHz$	C_{iss}	---	872	---	pF
Output Capacitance		C_{oss}	---	48	---	
Reverse Transfer Capacitance		C_{rss}	---	5.3	---	

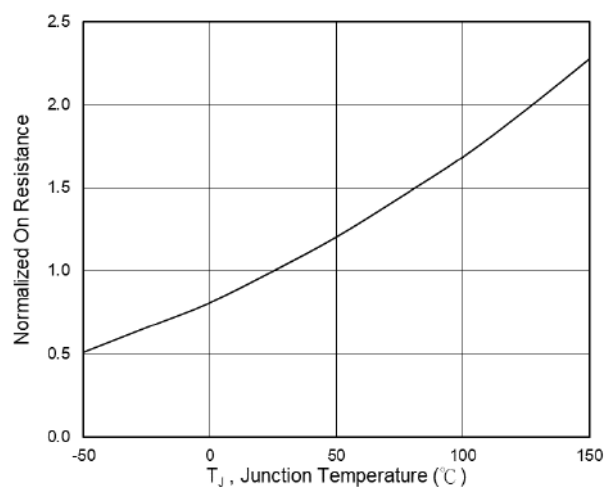
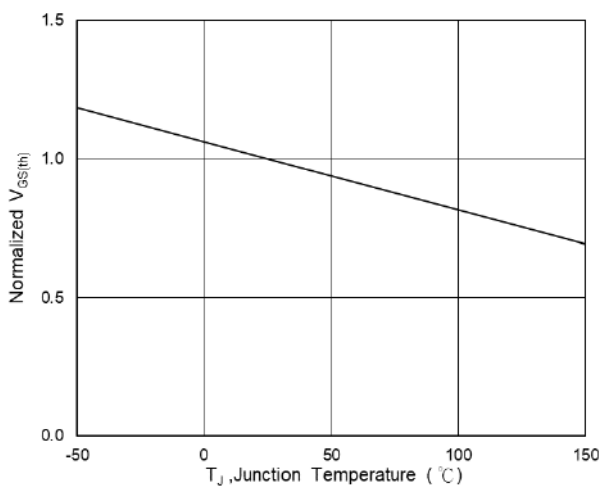
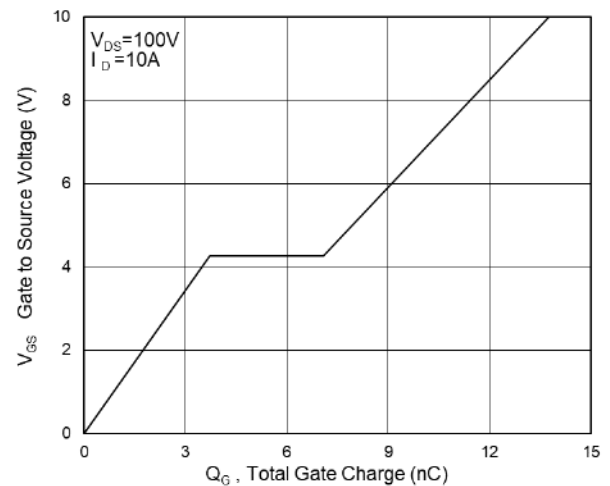
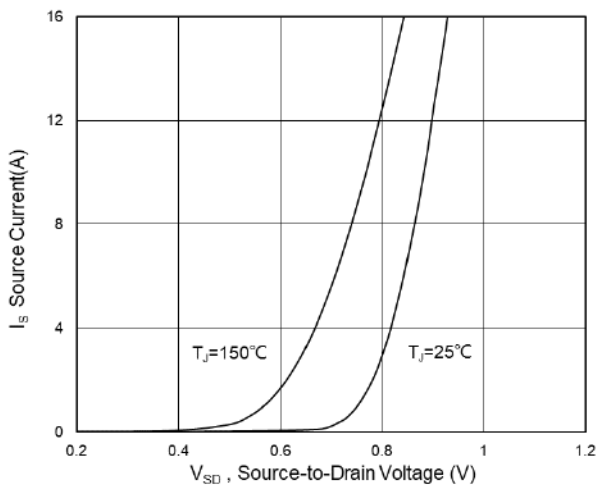
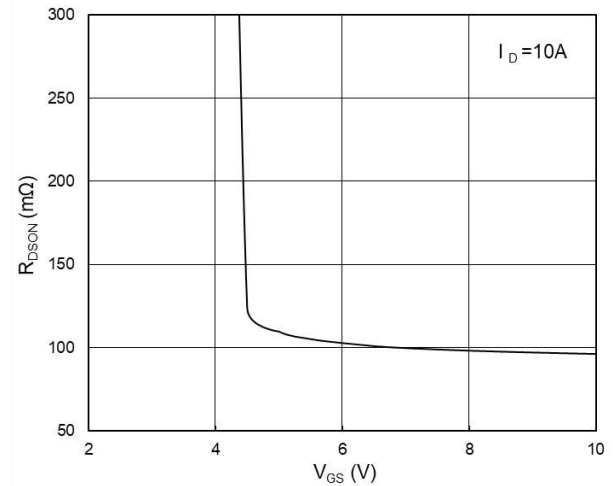
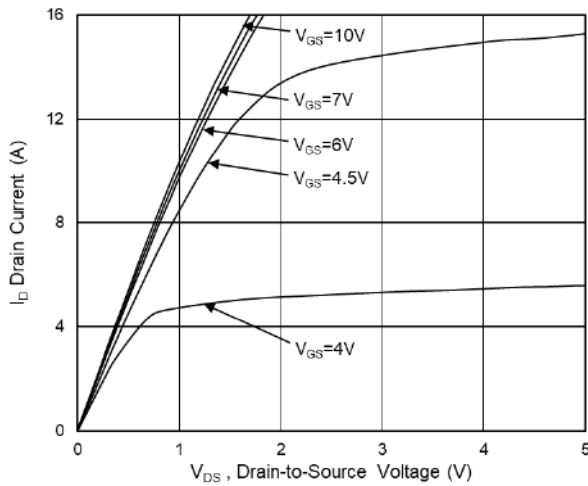
➤ Diode Characteristics

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	I_S	---	---	16	A
Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ C$	V_{SD}	---	---	1.2	V
Reverse Recovery Time	$I_F=10A$, $di/dt=100A/\mu s$, $T_J=25^\circ C$	t_{rr}	---	86	---	nS
Reverse Recovery Charge		Q_{rr}	---	307	---	nC

Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=28A$
4. Ensure that the channel temperature does not exceed $150^\circ C$.
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

➤ Typical Characteristics



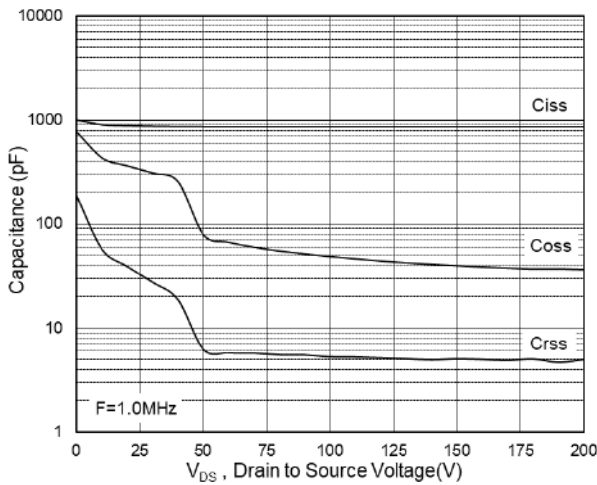


Fig.7 Capacitance

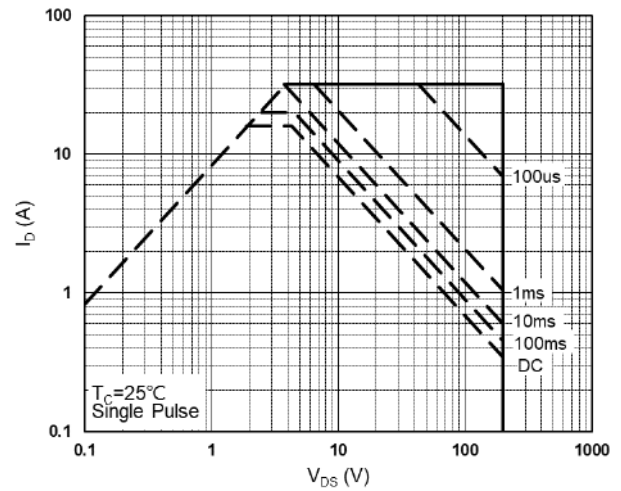


Fig.8 Safe Operating Area

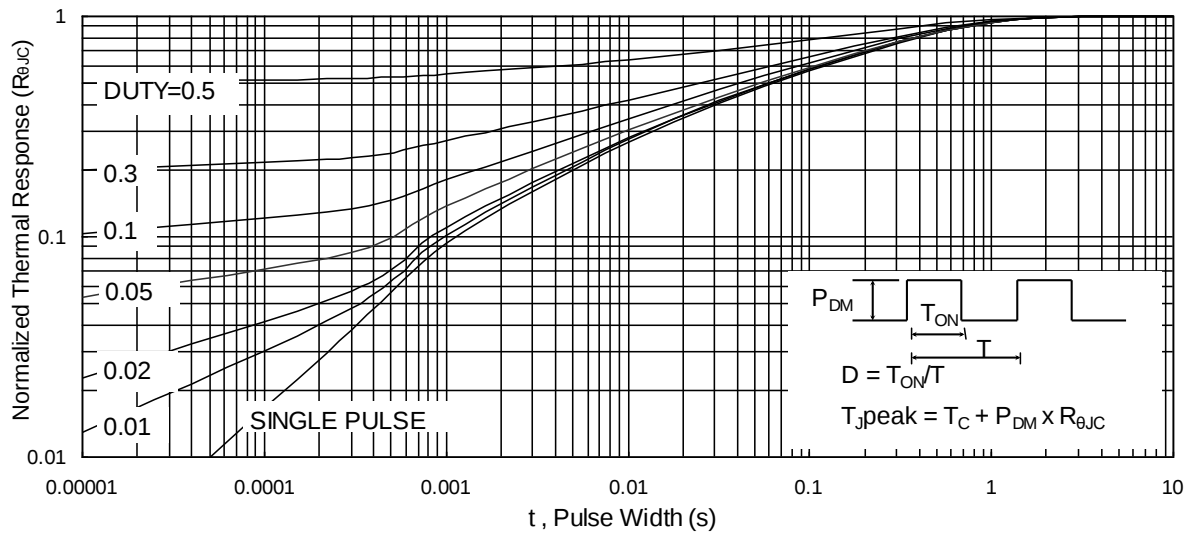


Fig.9 Normalized Maximum Transient Thermal Impedance

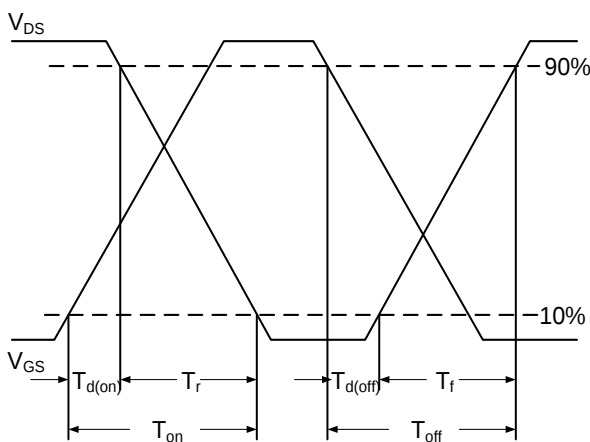


Fig.10 Switching Time Waveform

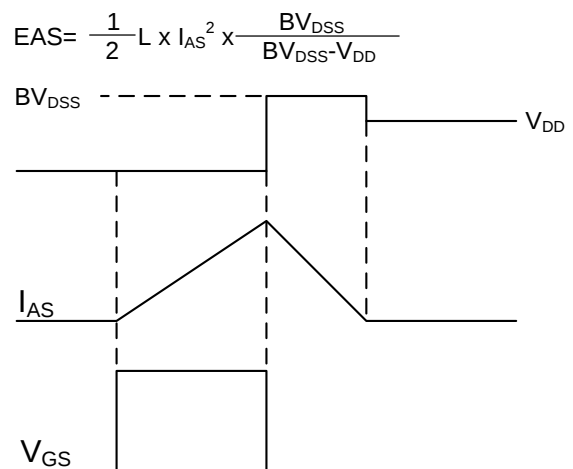
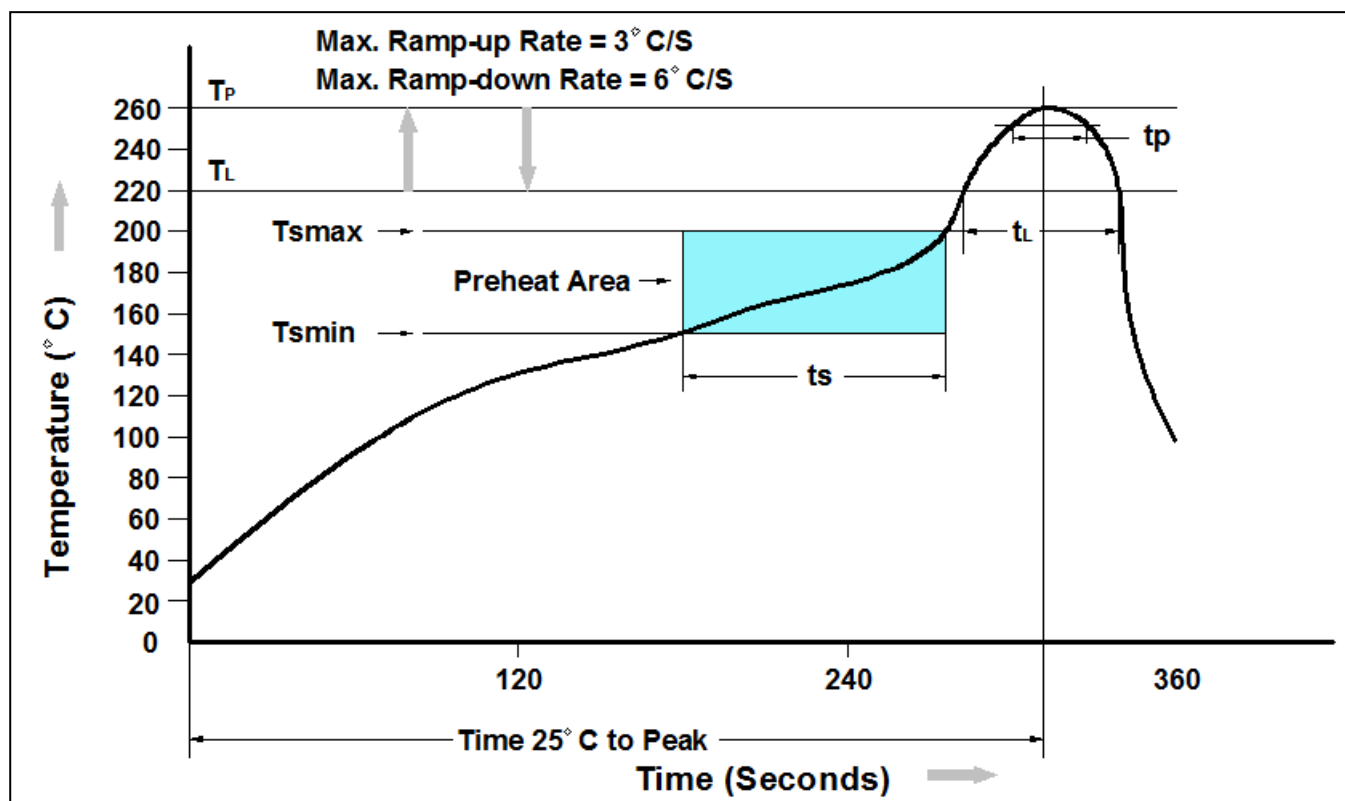


Fig.11 Unclamped Inductive Waveform

➤ Recommand IR Reflow Soldering Thermal Profile

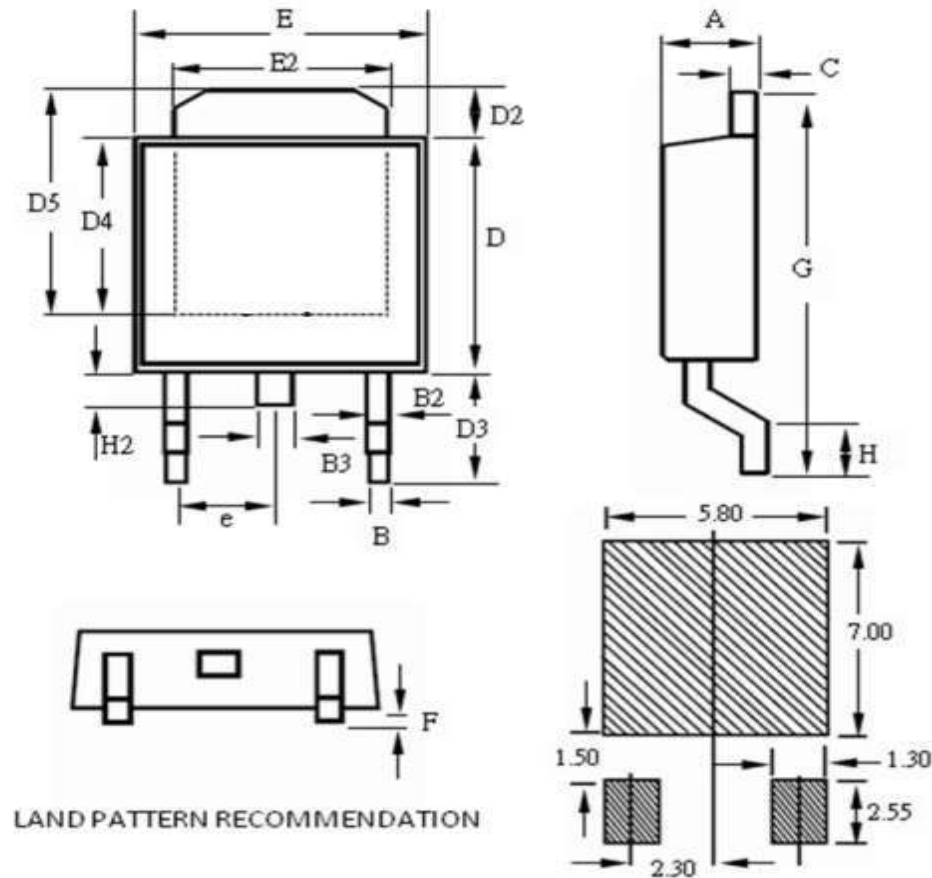


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{Smin})	150°C
Temperature Max. (T_{Smax})	200°C
Time (t_S) from (T_{Smin} to T_{Smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN18TX20AX	TO-252 Reel	2500 pcs

➤ Package Information (TO-252)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.10	--	2.50	0.083	--	0.098
B	0.30	--	0.89	0.012	--	0.035
B2	0.40	--	1.14	0.016	--	0.045
B3	0.60	--	1.00	0.024	--	0.039
C	0.40	--	0.89	0.016	--	0.035
D	5.30	--	6.25	0.209	--	0.246
D2	0.50	--	1.70	0.020	--	0.067
D3	2.20	--	3.40	0.087	--	0.134
D4	4.32	--	--	0.170	--	--
D5	5.21	--	--	0.205	--	--
E	6.30	--	6.73	0.248	--	0.265
E2	4.80	--	5.46	0.189	--	0.215
F	0.00	--	0.30	0.000	--	0.012
G	9.20	--	10.41	0.362	--	0.410
H	0.90	--	1.95	0.035	--	0.077
H2	0.50	--	1.10	0.020	--	0.043
e	--	2.30	--	--	0.091	--

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